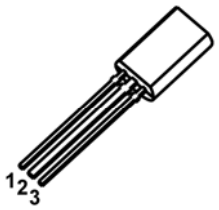
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

TO-92L

1. EMITTER
2. COLLECTOR
3. BASE



2SC2060 TRANSISTOR (NPN)

FEATURE

- Power Dissipation P_{CM}: 0.75 W (T_a=25℃)
- Low Saturation Voltage ($V_{CE(sat)}$=0.15V at 500mA)
- Complementary Pair with 2SA934

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage	40	V
V_{CEO}	Collector-Emitter Voltage	32	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Power Dissipation	750	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 100μA , I_E=0	40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 1mA , I_B=0	32		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}=20V , I_E=0		0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V , I_C=0		0.1	μA
DC current gain	h_{FE}	V_{CE}=3V, I_C= 100mA	80	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= 500m A, I_B= 50mA		0.4	V
Transition frequency	f_T	V_{CE}=5V, I_E=-50mA	50		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz		30	pF